# $\label{eq:additional} ADG733/ADG734 \\ -SPECIFICATIONS^{1}(v_{DD}=5 \ v \pm 10\%, \ v_{ss}=0 \ v, \ \text{GND}=0 \ v, \ \text{unless otherwise noted.})$

B Version		ersion		
Devenuestor	+25°C	-40°C	I lait	Test Conditions/Comments
Parameter	+25 C	to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH Analog Signal Range On Resistance (R <sub>ON</sub> )	2.5	0 V to $V_{DD}$	V Ω typ	$V_{\rm S} = 0 V$ to $V_{\rm DD}$ , $I_{\rm DS} = 10$ mA;
On Resistance Match between Channels ( $\Delta R_{ON}$ )	4.5	5.0 0.1 0.4	$\Omega$ max $\Omega$ typ $\Omega$ max	Test Circuit 1 $V_S = 0 V$ to $V_{DD}$ , $I_{DS} = 10 mA$
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	0.5	1.2	$\Omega$ typ $\Omega$ max	$V_{\rm S}$ = 0 V to $V_{\rm DD}$ , $I_{\rm DS}$ = 10 mA
LEAKAGE CURRENTS				$V_{DD} = 5.5 V$
Source OFF Leakage I <sub>S</sub> (OFF)	$\pm 0.01 \\ \pm 0.1$	±0.3	nA typ nA max	$V_D = 4.5 \text{ V/1 V}, V_S = 1 \text{ V/4.5 V};$ Test Circuit 2
Channel ON Leakage $I_{\rm D},I_{\rm S}$ (ON)	$\pm 0.01 \\ \pm 0.1$	±0.5	nA typ nA max	$V_D = V_S = 1 V$ , or 4.5 V; Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, V <sub>INH</sub>		2.4	V min	
Input Low Voltage, V <sub>INL</sub>		0.8	V max	
Input Current I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INL}$ or $V_{INH}$
C <sub>IN</sub> , Digital Input Capacitance	4	$\pm 0.1$	μA max pF typ	
DYNAMIC CHARACTERISTICS <sup>2</sup>				
t <sub>ON</sub>	19	34	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35 pF$ ; $V_S = 3 V$ , Test Circuit 4
t <sub>OFF</sub>	7		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF;$
ADG733 $t_{ON}(\overline{EN})$	20	12	ns max ns typ	$V_S = 3 V$ , Test Circuit 4 $R_L = 300 \Omega$ , $C_L = 35 pF$ ;
$t_{OFF}(\overline{EN})$	7	40	ns max ns typ	$V_s = 3 V$ , Test Circuit 5 $R_L = 300 \Omega$ , $C_L = 35 pF$ ;
		12	ns max	$V_{\rm S}$ = 3 V, Test Circuit 5
Break-Before-Make Time Delay, $t_D$	13	1	ns typ ns min	$R_L = 300 \Omega$ , $C_L = 35 pF$ ; $V_S = 3 V$ , Test Circuit 6
Charge Injection	±3	1	pC typ	$V_S = 5 V$ , lest chicuit o $V_S = 2 V$ , $R_S = 0 \Omega$ , $C_L = 1 nF$ ; Test Circuit 7
Off Isolation	-72		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; Test Circuit 8
Channel-to-Channel Crosstalk	-67		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; Test Circuit 9
–3 dB Bandwidth	160		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , Test Circuit 10
C <sub>S</sub> (OFF)	11		pF typ	f = 1 MHz
$C_{\rm D}, C_{\rm S}$ (ON)	34		pF typ	f = 1 MHz
POWER REQUIREMENTS				$V_{DD} = 5.5 V$
I <sub>DD</sub>	0.001	1.0	μA typ μA max	Digital Inputs = 0 V or 5.5 V

NOTES

<sup>1</sup>Temperature range is as follows: B Version: -40°C to +85°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# **SPECIFICATIONS**<sup>1</sup> ( $V_{DD} = 3 V \pm 10\%$ , $V_{SS} = 0 V$ , GND = 0 V, unless otherwise noted.)

	B Version -40°C				
Parameter	+25°C	to +85°C	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		$0 \text{ V}$ to $V_{\text{DD}}$	V		
On Resistance (R <sub>ON</sub> )	6		Ωtyp	$V_{S} = 0 V$ to $V_{DD}$ , $I_{DS} = 10 mA$ ;	
	11	12	$\Omega$ max	Test Circuit 1	
On Resistance Match between		0.1	Ω typ	$V_{S} = 0 V$ to $V_{DD}$ , $I_{DS} = 10 mA$	
Channels ( $\Delta R_{ON}$ )		0.4	$\Omega$ max		
On Resistance Flatness (R <sub>FLAT(ON)</sub> )		3	Ω typ	$V_{S} = 0 V$ to $V_{DD}$ , $I_{DS} = 10 mA$	
LEAKAGE CURRENTS				$V_{\rm DD} = 3.3  {\rm V}$	
Source OFF Leakage I <sub>S</sub> (OFF)	$\pm 0.01$		nA typ	$V_{\rm S} = 3 \text{ V/1 V}, V_{\rm D} = 1 \text{ V/3 V};$	
	$\pm 0.1$	±0.3	nA max	Test Circuit 2	
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)	$\pm 0.01$		nA typ	$V_{\rm S} = V_{\rm D} = 1$ V or 3 V;	
	±0.1	$\pm 0.5$	nA max	Test Circuit 3	
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>		2.0	V min		
Input Low Voltage, V <sub>INL</sub>		0.8	V max		
Input Current					
I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INL}$ or $V_{INH}$	
		$\pm 0.1$	µA max		
C <sub>IN</sub> , Digital Input Capacitance	4		pF typ		
DYNAMIC CHARACTERISTICS <sup>2</sup>					
t <sub>ON</sub>	28		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ;	
		55	ns max	$V_{\rm S}$ = 2 V, Test Circuit 4	
t <sub>OFF</sub>	9		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$	
		16	ns max	$V_{\rm S}$ = 2 V, Test Circuit 4	
ADG733 $t_{ON}(\overline{EN})$	29		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ;	
		60	ns max	$V_{\rm S}$ = 2 V, Test Circuit 5	
$t_{OFF}(\overline{EN})$	9		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ;	
		16	ns max	$V_s = 2 V$ , Test Circuit 5	
Break-Before-Make Time Delay, $t_D$	22		ns typ	$R_{\rm L} = 300 \ \Omega, \ C_{\rm L} = 35 \ \rm pF;$	
		1	ns min	$V_{\rm S} = 2 \text{ V}$ , Test Circuit 6	
Charge Injection	±3		pC typ	$V_S = 1 V, R_S = 0 \Omega, C_L = 1 nF;$	
Off Isolation	70		dD true	Test Circuit 7 $P_{1} = 500$ C = 5 pE f = 1 MHz	
On isolation	-72		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; Test Circuit 8	
Channel-to-Channel Crosstalk	-67		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ;	
				Test Circuit 9	
–3 dB Bandwidth	160		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , Test Circuit 10	
C <sub>S</sub> (OFF)	11		pF typ	f = 1 MHz	
$C_D, C_S$ (ON)	34		pF typ	f = 1 MHz	
POWER REQUIREMENTS				$V_{DD} = 3.3 V$	
I <sub>DD</sub>	0.001		μA typ	Digital Inputs = $0 \text{ V or } 3.3 \text{ V}$	
		1.0	µA max		

NOTES

<sup>1</sup>Temperature ranges are as follows: B Version: -40°C to +85°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# ADG733/ADG734-SPECIFICATIONS<sup>1</sup>

**DUAL SUPPLY** ( $V_{DD} = +2.5 V \pm 10\%$ ,  $V_{SS} = -2.5 V \pm 10\%$ , GND = 0 V, unless otherwise noted.)

	B Version				
Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		$V_{SS}$ to $V_{DD}$	V		
On Resistance (R <sub>ON</sub> )	2.5		$\Omega$ typ	$V_{S} = V_{SS}$ to $V_{DD}$ , $I_{DS} = 10$ mA;	
	4.5	5.0	$\Omega$ max	Test Circuit 1	
On Resistance Match between		0.1	Ω typ	$V_{S} = V_{SS}$ to $V_{DD}$ , $I_{DS} = 10 \text{ mA}$	
Channels ( $\Delta R_{ON}$ )		0.4	$\Omega$ max		
On Resistance Flatness (R <sub>FLAT(ON)</sub> )	0.5		Ω typ	$V_{S} = V_{SS}$ to $V_{DD}$ , $I_{DS} = 10 \text{ mA}$	
		1.2	$\Omega$ max		
LEAKAGE CURRENTS				$V_{DD}$ = +2.75 V, $V_{SS}$ = -2.75 V	
Source OFF Leakage I <sub>S</sub> (OFF)	±0.01		nA typ	$V_{\rm S}$ = +2.25 V/-1.25 V, $V_{\rm D}$ = -1.25 V/+2.25 V	
	±0.1	±0.3	nA max	Test Circuit 2	
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)	±0.01		nA typ	$V_{\rm S} = V_{\rm D} = +2.25 \text{ V/}-1.25 \text{ V}$ , Test Circuit 3	
	±0.1	$\pm 0.5$	nA max		
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>		1.7	V min		
Input Low Voltage, V <sub>INL</sub>		0.7	V max		
Input Current					
I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INL}$ or $V_{INH}$	
		$\pm 0.1$	μA max		
C <sub>IN</sub> , Digital Input Capacitance	4		pF typ		
DYNAMIC CHARACTERISTICS <sup>2</sup>					
t <sub>ON</sub>	21		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$ ;	
		35	ns max	$V_s = 1.5 V$ , Test Circuit 4	
t <sub>OFF</sub>	10		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$	
		16	ns max	$V_s = 1.5 V$ , Test Circuit 4	
ADG733 $t_{ON}(\overline{EN})$	21		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$	
		40	ns max	$V_s = 1.5 V$ , Test Circuit 5	
$t_{OFF}(\overline{EN})$	10		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$	
		16	ns max	$V_S = 1.5 V$ , Test Circuit 5	
Break-Before-Make Time Delay, $t_D$	13		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$	
		1	ns min	$V_s = 1.5 V$ , Test Circuit 6	
Charge Injection	±5		pC typ	$V_{\rm S} = 0 \text{ V},        $	
				Test Circuit 7	
Off Isolation	-72		dB typ	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz;$	
				Test Circuit 8 P = 500, C = 5, F = 1, MH	
Channel-to-Channel Crosstalk	-67		dB typ	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz;$	
-3 dB Bandwidth	200			Test Circuit 9 $P_{r} = 50 \Omega_{r} C_{r} = 5 p F_{r}$ Test Circuit 10	
$-3$ dB Bandwidth $C_{S}$ (OFF)	200 11		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , Test Circuit 10 f = 1 MHz	
$C_{\rm S}$ (OFF) $C_{\rm D}$ , $C_{\rm S}$ (ON)	34		pF typ pF typ	f = 1 MHz	
			prityp		
POWER REQUIREMENTS	0.001			$V_{DD} = 2.75 V$	
I <sub>DD</sub>	0.001	1.0	μA typ	Digital Inputs = 0 V or 2.75 V	
T	0.001	1.0	μA max		
I <sub>SS</sub>	0.001	1.0	μA typ	$V_{SS} = -2.75 V$	
		1.0	μA max	Digital Inputs = 0 V or 2.75 V	

NOTES

<sup>1</sup>Temperature range is as follows: B Version: -40°C to +85°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

#### ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

$(T_A = 25^{\circ}C, \text{ unless otherwise noted.})$
$V_{DD}$ to $V_{SS}$ $\hfill \ldots \hfill 7$ V
$V_{DD}$ to GND
$V_{SS}$ to GND
Analog Inputs <sup>2</sup> $V_{SS} - 0.3$ V to $V_{DD} + 0.3$ V or
30 mA, Whichever Occurs First
Digital Inputs <sup>2</sup> $-0.3$ V to V <sub>DD</sub> + 0.3 V or
30 mA, Whichever Occurs First
Peak Current, S or D 100 mA
(Pulsed at 1 ms, 10% Duty Cycle max)
Continuous Current, S or D 30 mA
Operating Temperature Range
Industrial (A, B Versions) $\dots -40^{\circ}$ C to $+85^{\circ}$ C
Storage Temperature Range65°C to +150°C

Junction Temperature 150°C
16-Lead TSSOP, $\theta_{IA}$ Thermal Impedance 150.4°C/W
20-Lead TSSOP, $\theta_{IA}$ Thermal Impedance 143°C/W
16-Lead QSOP, θ <sub>IA</sub> Thermal Impedance 149.97°C/W
Lead Temperature, Soldering (10 sec) 300°C
IR Reflow, Peak Temperature (<20 sec) 235°C
NOTES

<sup>1</sup> Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>2</sup> Overvoltages at A, EN, IN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

#### CAUTION -

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG733/ADG734 feature proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



#### **PIN CONFIGURATIONS**

### TSSOP/QSOP

#### TSSOP

					1
г		1	IN1 1	•	20 IN4
S2B 1	•	16 V <sub>DD</sub>	S1A 2		19 S4A
S2A 2		15 D2	D1 3	1	18 D4
S3B 3	ADG733	14 D1	S1B 4	ADG734	17 S4B
D3 4		13 S1B	V <sub>SS</sub> 5	TOP VIEW (Not to Scale)	16 V <sub>DD</sub>
S3A 5	(Not to Scale)	12 S1A	GND 6	(NOT to Scale)	15 NC
EN 6		11 A0	S2B 7		14 S3B
V <sub>SS</sub> 7		10 A1	D2 8		13 D3
GND 8		9 A2	S2A 9		12 S3A
L		J	IN2 10		11 IN3

NC = NO CONNECT

A2	A1	A0	EN	ON Switch
Х	X	X	1	None
0	0	0	0	D1-S1A, D2-S2A, D3-S3A
0	0	1	0	D1-S1B, D2-S2A, D3-S3A
0	1	0	0	D1-S1A, D2-S2B, D3-S3A
0	1	1	0	D1-S1B, D2-S2B, D3-S3A
1	0	0	0	D1-S1A, D2-S2A, D3-S3B
1	0	1	0	D1-S1B, D2-S2A, D3-S3B
1	1	0	0	D1-S1A, D2-S2B, D3-S3B
1	1	1	0	D1-S1B, D2-S2B, D3-S3B

#### Table I. ADG733 Truth Table

X = Don't Care.

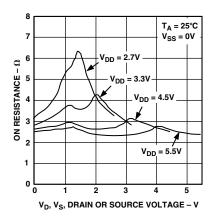
#### TERMINOLOGY

V <sub>DD</sub>	Most Positive Power Supply Potential
V <sub>SS</sub>	Most Negative Power Supply in a Dual Supply Application. In single supply applications, this should be tied to ground close to the device.
I <sub>DD</sub>	Positive Supply Current
I <sub>SS</sub>	Negative Supply Current
GND	Ground (0 V) Reference
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
A <sub>X</sub>	Logic Control Input
ĒN	Active low device enable
$V_D (V_S)$	Analog Voltage on Terminals D and S
R <sub>ON</sub>	Ohmic Resistance between D and S
$\Delta R_{ON}$	On Resistance Match between any Two Channels (i.e., R <sub>ON</sub> max and R <sub>ON</sub> min)
R <sub>FLAT(ON)</sub>	Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.
I <sub>S</sub> (OFF)	Source Leakage Current with the Switch "OFF"
$I_D$ , $I_S$ (ON)	Channel Leakage Current with the Switch "ON"
V <sub>INL</sub>	Maximum Input Voltage for Logic "0"
V <sub>INH</sub>	Minimum Input Voltage for Logic "1"
$I_{INL}(I_{INH})$	Input Current of the Digital Input
C <sub>S</sub> (OFF)	"OFF" Switch Source Capacitance. Measured with reference to ground.
$C_D, C_S(ON)$	"ON" Switch Capacitance. Measured with reference to ground.
C <sub>IN</sub>	Digital Input Capacitance
t <sub>ON</sub>	Delay Time Measured between the 50% and 90% Points of the Digital Inputs and the Switch "ON" Condition
t <sub>OFF</sub>	Delay Time Measured between the 50% and 90% Points of the Digital Input and the Switch "OFF" Condition
$t_{ON}(\overline{EN})$	Delay Time between the 50% and 90% Points of the EN Digital Input and the Switch "ON" Condition
$t_{OFF}(\overline{EN})$	Delay Time between the 50% and 90% Points of the EN Digital Input and the Switch "OFF" Condition
t <sub>OPEN</sub>	"OFF" Time Measured between the 80% Points of Both Switches when Switching from One Address State to Another
Charge	A Measure of the Glitch Impulse Transferred Injection from the Digital Input to the Analog Output during Switching
Off Isolation	A Measure of Unwanted Signal Coupling through an "OFF" Switch.
Crosstalk	A Measure of Unwanted Signal that Is Coupled through from One Channel to Another as a Result of Para- sitic Capacitance
On Response	The Frequency Response of the "ON" Switch
Insertion Loss	The Loss Due to the On Resistance of the switch

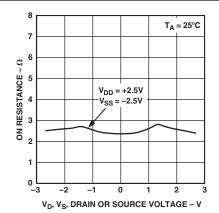
#### Table II. ADG734 Truth Table

Logic	Switch A	Switch B
0	OFF	ON
1	ON	OFF

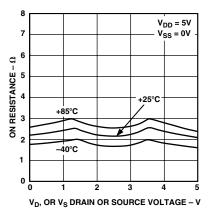
# Typical Performance Characteristics-ADG733/ADG734



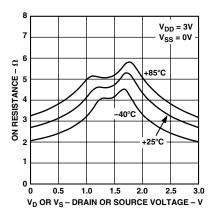
TPC 1. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Single Supply



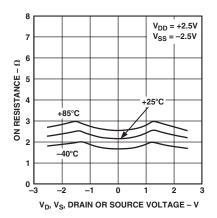
TPC 2. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Dual Supply



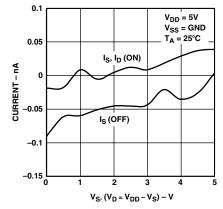
TPC 3. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, Single Supply



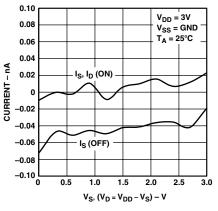
TPC 4. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, Single Supply



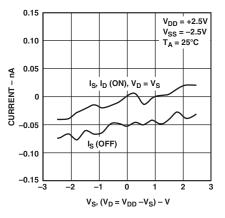
TPC 5. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, Dual Supply



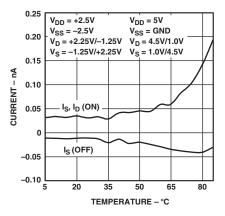
TPC 6. Leakage Currents as a Function of  $V_D$  ( $V_S$ )



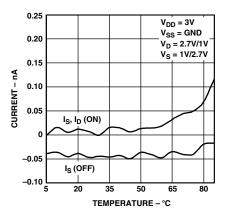
TPC 7. Leakage Currents as a Function of  $V_D$  ( $V_S$ )



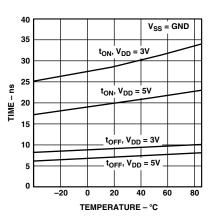
TPC 8. Leakage Currents as a Function of  $V_D$  ( $V_S$ )



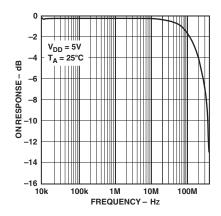
*TPC 9. Leakage Currents as a Function of Temperature* 



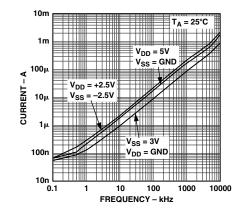
*TPC 10. Leakage Currents as a Function of Temperature* 



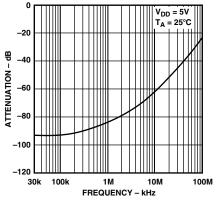
TPC 11. t<sub>ON</sub>/t<sub>OFF</sub> Times vs. Temperature



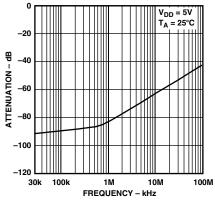
TPC 12. On Response vs. Frequency



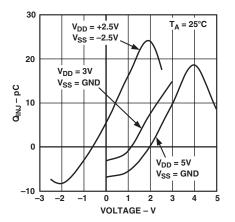
TPC 13. Input Current, I<sub>DD</sub> vs. Switching Frequency



TPC 14. Off Isolation vs. Frequency

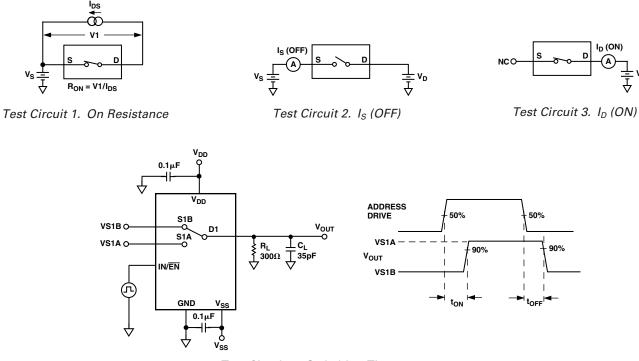


TPC 15. Crosstalk vs. Frequency

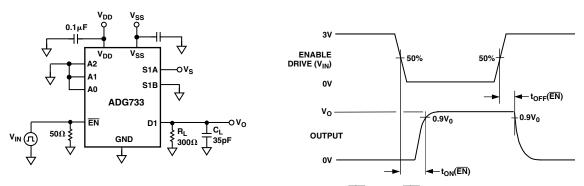


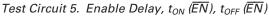
TPC 16. Charge Injection vs. Source Voltage

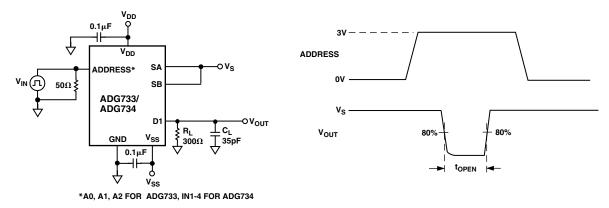
# **Test Circuits**



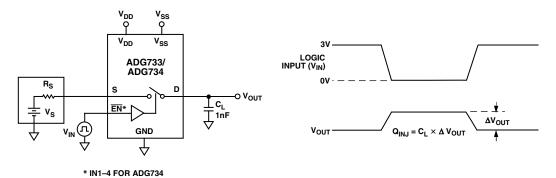




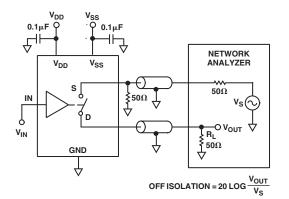




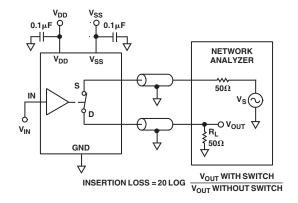
Test Circuit 6. Break-Before-Make Delay, t<sub>OPEN</sub>



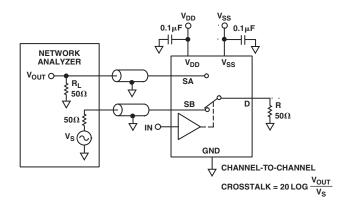
Test Circuit 7. Charge Injection



Test Circuit 8. Off Isolation



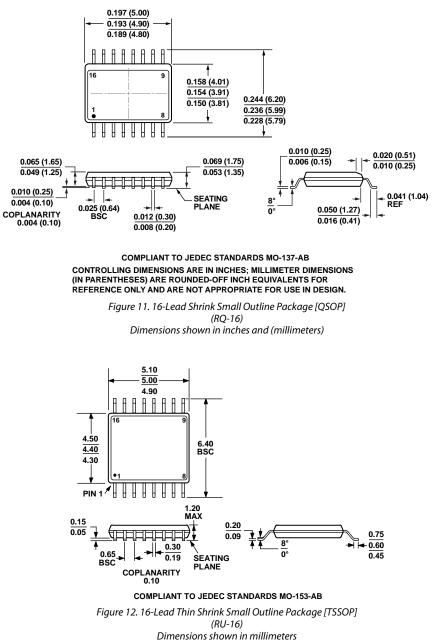
Test Circuit 10. Bandwidth

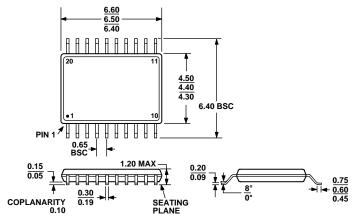


Test Circuit 9. Channel-to-Channel Crosstalk

01-28-2008-A

### **OUTLINE DIMENSIONS**





COMPLIANT TO JEDEC STANDARDS MO-153-AC

Figure 13. 20-Lead Thin Shrink Small Outline Package [TSSOP]

(RU-20)

Dimensions shown in millimeters

#### **ORDERING GUIDE**

Model <sup>1</sup>	Temperature Range	Package Description	Package Option
ADG733BRQZ	-40°C to +85°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG733BRQZ-REEL	-40°C to +85°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG733BRU-REEL7	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG733BRUZ	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG733BRUZ-REEL	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG733BRUZ-REEL7	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG734BRU	-40°C to +85°C	20-Lead Thin Shrink Small Outline Package [TSSOP]	RU-20
ADG734BRU-REEL	-40°C to +85°C	20-Lead Thin Shrink Small Outline Package [TSSOP]	RU-20
ADG734BRUZ	-40°C to +85°C	20-Lead Thin Shrink Small Outline Package [TSSOP]	RU-20
ADG734BRUZ-REEL	-40°C to +85°C	20-Lead Thin Shrink Small Outline Package [TSSOP]	RU-20
ADG734BRUZ-REEL7	-40°C to +85°C	20-Lead Thin Shrink Small Outline Package [TSSOP]	RU-20

 $^{1}$  Z = RoHS Compliant Part.

#### **REVISION HISTORY**

#### 4/14—Rev. A to Rev. B

Updated Outline Dimensions 11
Changes to Ordering Guide 12
11/02—Data Sheet changed from REV. 0 to REV. A.
Changes to FEATURES 1
Changes to PRODUCT HIGHLIGHTS 1
Changes to SPECIFICATIONS 2
Changes to ABSOLUTE MAXIMUM RATINGS Note 2
Changes to TERMINOLOGY table
Replaced TPCs 2, 5, 8, and 97
Edits to TPCs 6 and 77
Replaced TPC 12 8
Edits to TPCs 13 and 16
Replaced Test Circuits 8 and 910
Added Test Circuit 10 10
Updated OUTLINE DIMENSIONS 11

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